

## **AMENDMENTS TO THE CLAIMS**

The following listing of claims replaces all prior listings and versions of claims in this application.

1. (Previously Presented) A method for forming an assembly for transfer of a useful layer comprising:  
forming a useful layer on a first support having an interface therebetween, and  
forming a residual material on a portion of the first support to form the assembly; and  
processing the first support to attenuate bonding between the useful layer and the first support caused by the residual material;  
wherein processing of the first support comprises forming a peripheral recess on the first support so that the residual material does not contact the useful layer.
2. (Original) The method of claim 1 wherein the useful layer is weakly bonded to the support to facilitate detachment.
3. (Original) The method of claim 1 wherein the interface is a detachable interface layer provided on the first support before forming the useful layer.
4. (Original) The method of claim 1 which further comprises:  
affixing a free face of the useful layer to a second support; and  
detaching the useful layer at the interface to transfer the useful layer to the second support.
5. (Original) The method of claim 4 which further comprises detaching the useful layer by using at least one of tension forces, bending forces and shear stress forces.
6. (Original) The method of claim 4 which further comprises directing at least one of a thin blade or a jet of fluid to the interface layer to detach the useful layer.
7. (Previously Presented) The method of claim 1 wherein processing the first support comprises removing residual material.
8. (Original) The method of claim 7 which further comprises removing at least a portion of the first support that is in contact with the removed residual material.

9. (Original) The method of claim 7 wherein removing residual material comprises removing at least a portion of a peripheral zone of residual material covering an edge of the interface.

10. (Original) The method of claim 9 wherein the peripheral zone is removed by at least one of splitting or etching.

11. (Original) The method of claim 10 wherein the peripheral zone is removed by etching and which further comprises masking the useful layer prior to etching.

12. (Previously Presented) The method of claim 1 wherein the recess is at least one cut or separating channel between a free surface of the useful layer and the interface to separate the useful layer from the residual material.

13. (Original) The method of claim 12 wherein the separating channel is cut by using at least one of a saw splitting technique, a laser splitting technique, and an ion beam splitting and masked chemical etching technique.

14. (Previously Presented) The method of claim 12 which further comprises forming a plurality of cuts or separating channels in the useful layer to form a plurality of useful layer islets.

15. (Original) The method of claim 14 which further comprises:  
affixing free faces of the islets to a second support; and  
detaching a majority of the islets at the interface.

16. (Original) The method of claim 15 which further comprises detaching the islets by using at least one of tension forces, bending forces and shear stress forces.

17. (Original) The method of claim 15 wherein the islets are rectangular.

Claim 18. (Cancelled)

19. (Previously Presented) The process of claim 1, wherein the width and depth of the peripheral recess is sufficient to accommodate the volume of residual material resulting from formation of the useful layer.

20. (Original) The method of claim 1 which further comprises using full wafer epitaxy to deposit at least a portion of the useful layer.

21. (Original) The method of claim 20 wherein the useful layer comprises a seed layer for epitaxial growth and at least one epitaxial layer.

22. (Original) The method of claim 21 wherein the seed layer is made of at least one of silicon carbide, sapphire, gallium nitride, silicon and aluminum nitride.

23. (Original) The method of claim 21 wherein the epitaxial layer is formed from one or more metal nitrides.

24. (Original) The method of claim 1 wherein the first support is made from at least one of a semiconductor, a semiconducting or semiconductive carbide, and an insulator material.

25. (Original) The method of claim 1 which further comprises providing the interface by at least one of implanting gas species, forming a porous layer that can be attacked chemically, and bonding a detachable layer to the first support before forming the useful layer by using a controlled molecular bonding process.

Claims 26. to 28. (Cancelled)

29. (Previously Presented) A method for forming an assembly for transfer of a useful layer comprising:

forming a peripheral recess on a support; and

forming a useful layer on the support while also forming a residual material on a portion of the support to form the assembly;

wherein the peripheral recess has a width and depth sufficient to accommodate the volume of residual material resulting from formation of the useful layer so that the residual material does not contact the useful layer.

30. (New) The method of claim 1 wherein the useful layer comprises a seed layer for epitaxial growth and at least one epitaxial layer that forms the residual material.

31. (New) The method of claim 30 wherein the seed layer is made of at least one of silicon carbide, sapphire, gallium nitride, silicon and aluminum nitride, and

32. (New) The method of claim 30 wherein the epitaxial layer is formed from one or more metal nitrides.